

HEF4517B

Dual 64-bit static shift register

Rev. 06 — 10 December 2009

Product data sheet

1. General description

The HEF4517B consists of two identical, independent 64-bit static shift registers. Each register has separate clock (nCP), data input (nD), parallel input-enable/output-enable (nPE/OE) and four 3-state outputs of the 16th, 32nd, 48th, and 64th bit positions (nQ16 to nQ64). Data at the nD input is entered into the first bit on the LOW-to-HIGH transition of the clock, regardless of the state of nPE/OE.

When nPE/OE is LOW, the outputs are enabled and it is in the 64-bit serial mode.

When nPE/OE is HIGH, the outputs are disabled (high-impedance OFF-state), the 64-bit shift register is divided into four 16-bit shift registers with nD, nQ16, nQ32 and nQ48 as data inputs of the 1st, 17th, 33rd, and 49th bit respectively. Schmitt-trigger action in the clock input makes the circuit highly tolerant of slower clock rise and fall times.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input. It is also suitable for use over the full industrial (−40 °C to +85 °C) temperature range.

2. Features

- Tolerant of slow clock rise and fall times
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Operates across the full industrial temperature range −40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

3. Applications

- Industrial

4. Ordering information

Table 1. Ordering information

All types operate from −40 °C to +85 °C

Type number	Package		
	Name	Description	Version
HEF4517BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
HEF4517BT	SO16	plastic small outline package; 16 leads; body width 7.5 mm	SOT162-1

5. Functional diagram

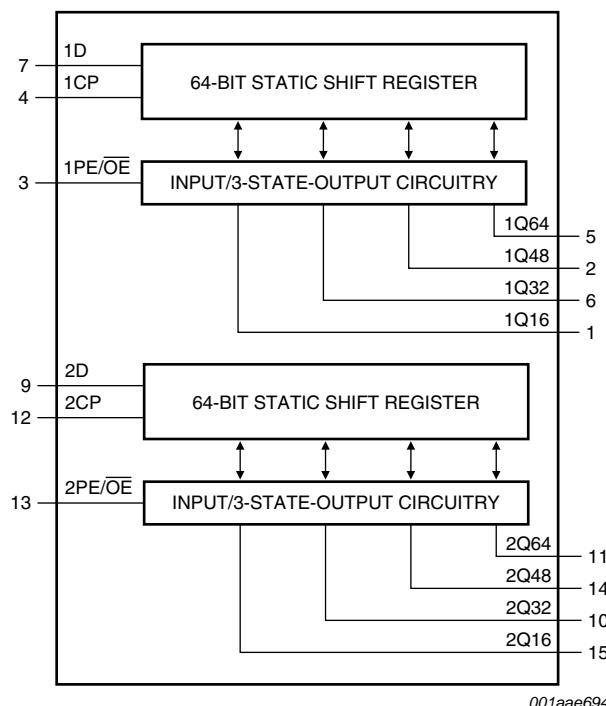
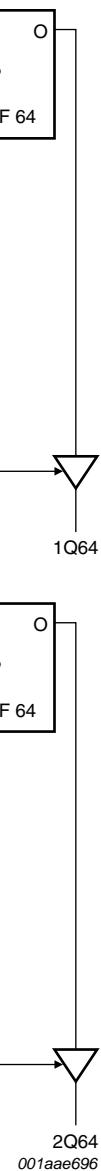
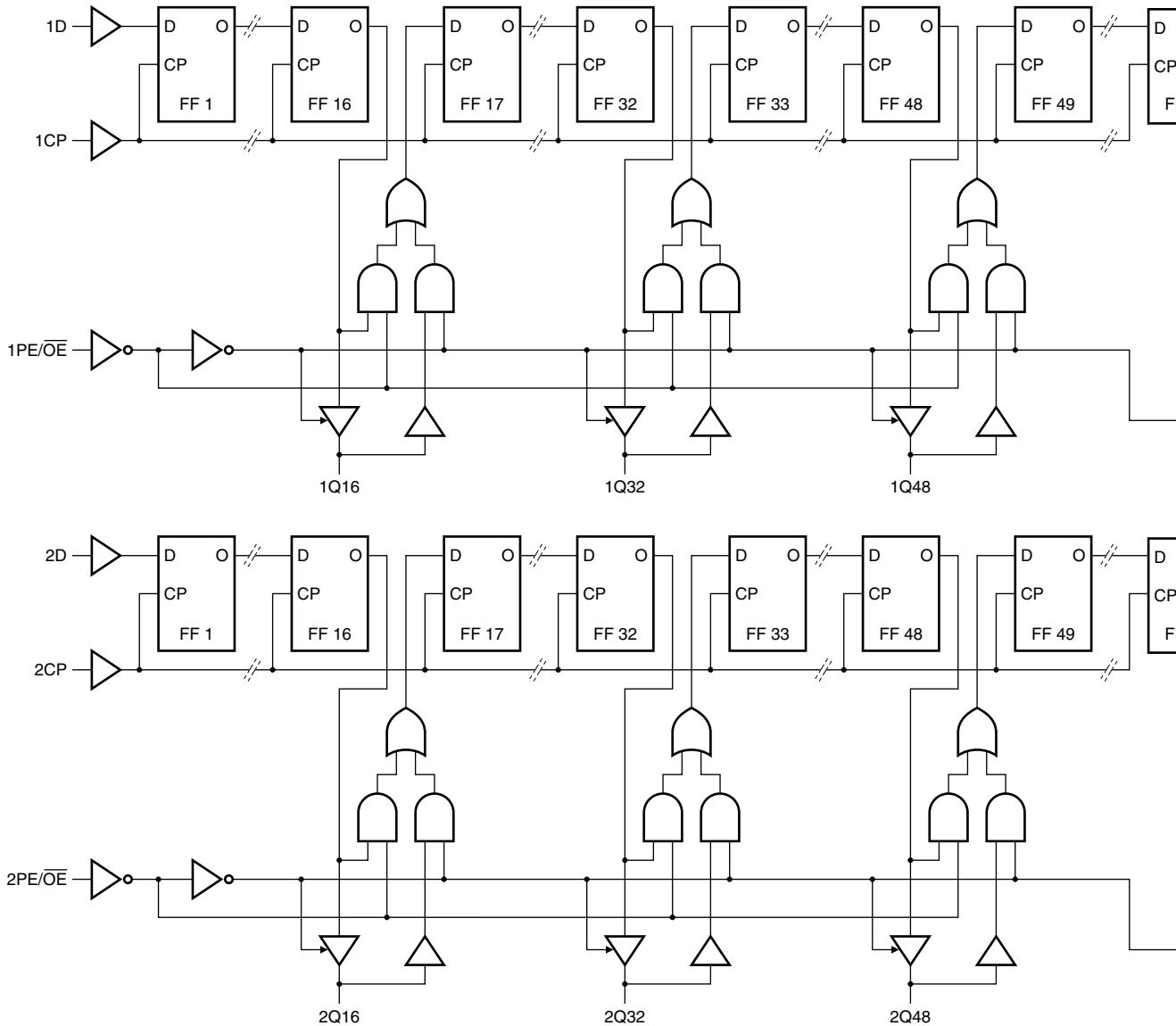


Fig 1. Functional diagram

Dual 64-bit static shift register



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Fig 2. Logic diagram

6. Pinning information

6.1 Pinning

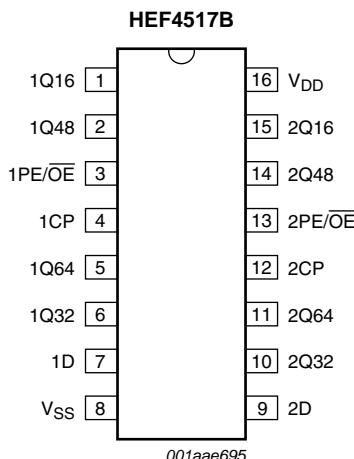


Fig 3. Pin configuration

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Q16, 2Q16	1, 15	3-state input/output
1Q48, 2Q48	2, 14	3-state input/output
1PE/OE, 2PE/OE	3, 13	parallel input-enable/output-enable input
1CP, 2CP	4, 12	clock input
1Q64, 2Q64	5, 11	3-state input/output
1Q32, 2Q32	6, 10	3-state input/output
1D, 2D	7, 9	data input
V _{ss}	8	ground supply voltage
V _{dd}	16	supply voltage

7. Functional description

Table 3. Function table^[1]

Inputs			Inputs/outputs				Mode
nCP	nD	nPE/OE	nQ16	nQ32	nQ48	nQ64	
↑	data entered L into 1st bit		content of 16th bit displayed	content of 32nd bit displayed	content of 48th bit displayed	content of 64th bit displayed	One 64-bit shift register. The content of the shift register is shifted over one stage
↑	data entered H into 1st bit		data at nQ16 entered into 17th bit	data at nQ32 entered into 33rd bit	data at nQ48 entered into 49th bit	remains in 'Z' state	Four 16-bit shift register. The content of the shift registers is shifted over one stage
↓	X	L	no change	no change	no change	no change	no change
↓	X	H	Z	Z	Z	Z	no change

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance state;
 ↑ = positive-going transition; ↓ = negative-going transition.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{DD} + 0.5 V	-	±10	mA
V _I	input voltage		-0.5	V _{DD} + 0.5	V
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{DD} + 0.5 V	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I _{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	total power dissipation	DIP16 package	^[1] -	750	mW
		SO16 package	^[2] -	500	mW
P	power dissipation	per output	-	100	mW

[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5\text{ V}$	-	-	3.75	μs/V
		$V_{DD} = 10\text{ V}$	-	-	0.5	μs/V
		$V_{DD} = 15\text{ V}$	-	-	0.08	μs/V

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = 25\text{ °C}$		$T_{amb} = 85\text{ °C}$		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage $ I_O < 1\text{ μA}$		5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage $ I_O < 1\text{ μA}$		5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V_{OH}	HIGH-level output voltage $ I_O < 1\text{ μA}$		5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage $ I_O < 1\text{ μA}$		5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current $V_O = 2.5\text{ V}$		5 V	-1.7	-	-1.4	-	-1.1	-	mA
			5 V	-0.52	-	-0.44	-	-0.36	-	mA
			10 V	-1.3	-	-1.1	-	-0.9	-	mA
			15 V	-3.6	-	-3.0	-	-2.4	-	mA
I_{OL}	LOW-level output current $V_O = 0.4\text{ V}$		5 V	0.52	-	0.44	-	0.36	-	mA
			10 V	1.3	-	1.1	-	0.9	-	mA
			15 V	3.6	-	3.0	-	2.4	-	mA
I_I	input leakage current		15 V	-	±0.3	-	±0.3	-	±1.0	μA
I_{DD}	supply current $I_O = 0\text{ A}$		5 V	-	50	-	50	-	375	μA
			10 V	-	100	-	100	-	750	μA
			15 V	-	200	-	200	-	1500	μA
C_I	input capacitance		-	-	-	-	7.5	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics $V_{SS} = 0 \text{ V}$; $T_{amb} = 25^\circ\text{C}$; for test circuit see [Figure 8](#); unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	nCP to nQn; see Figure 4	5 V	[1] 193 ns + (0.55 ns/pF) C_L	-	220	440	ns
			10 V	74 ns + (0.23 ns/pF) C_L	-	85	170	ns
			15 V	52 ns + (0.16 ns/pF) C_L	-	60	120	ns
t_{PLH}	LOW to HIGH propagation delay	nCP to nQn; see Figure 4	5 V	[1] 163 ns + (0.55 ns/pF) C_L	-	190	380	ns
			10 V	64 ns + (0.23 ns/pF) C_L	-	75	150	ns
			15 V	42 ns + (0.16 ns/pF) C_L	-	50	100	ns
t_{PZH}	HIGH to OFF-state propagation delay	nPE/ \overline{OE} to nQn; see Figure 5	5 V		-	40	80	ns
			10 V		-	30	60	ns
			15 V		-	25	50	ns
t_{PZL}	OFF-state to HIGH propagation delay	nPE/ \overline{OE} to nQn; see Figure 5	5 V		-	45	90	ns
			10 V		-	25	50	ns
			15 V		-	20	40	ns
t_{PLZ}	LOW to OFF-state propagation delay	nPE/ \overline{OE} to nQn; see Figure 5	5 V		-	50	100	ns
			10 V		-	30	60	ns
			15 V		-	25	50	ns
t_{PZL}	OFF-state to LOW propagation delay	nPE/ \overline{OE} to nQn; see Figure 5	5 V		-	60	120	ns
			10 V		-	30	60	ns
			15 V		-	25	50	ns
t_t	transition time	nQn; see Figure 6	5 V	[1] 10 ns + (1.00 ns/pF) C_L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF) C_L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF) C_L	-	20	40	ns
t_{su}	set-up time	nQn, nD to nCP; see Figure 7	5 V		30	10	-	ns
			10 V		25	5	-	ns
			15 V		20	5	-	ns
t_h	hold time	nQn, nD to nCP; see Figure 7	5 V		45	15	-	ns
			10 V		30	10	-	ns
			15 V		25	10	-	ns
t_w	pulse width	nQn, nD to nCP; see Figure 7	5 V		-	95	190	ns
			10 V		-	40	80	ns
			15 V		-	30	60	ns
f_{max}	maximum frequency	see Figure 7	5 V		2	5	-	MHz
			10 V		6	12	-	MHz
			15 V		8	16	-	MHz

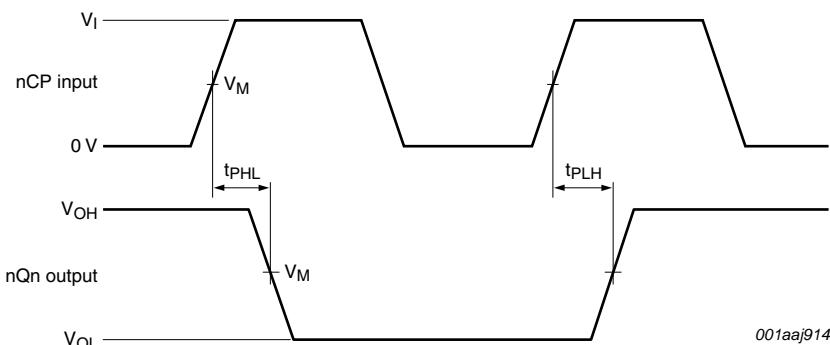
[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Table 8. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown. $V_{SS} = 0 \text{ V}$; $t_r = t_f \leq 20 \text{ ns}$; $T_{amb} = 25^\circ\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	where:
P_D	dynamic power dissipation	5 V	$P_D = 7000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz,
		10 V	$P_D = 28000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_o = output frequency in MHz,
		15 V	$P_D = 70000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\Sigma(f_o \times C_L)$ = sum of the outputs.

12. Waveforms



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Measurement points are given in [Table 9](#)

The logic levels V_{OH} and V_{OL} are typical voltage output levels that occur with the output load.

Fig 4. Propagation delays for nCP to nQn**Table 9. Measurement points**

Input	Output		
V_M	V_M	V_X	V_Y
$0.5V_I$	$0.5V_{DD}$	$0.1V_{DD}$	$0.9V_{DD}$

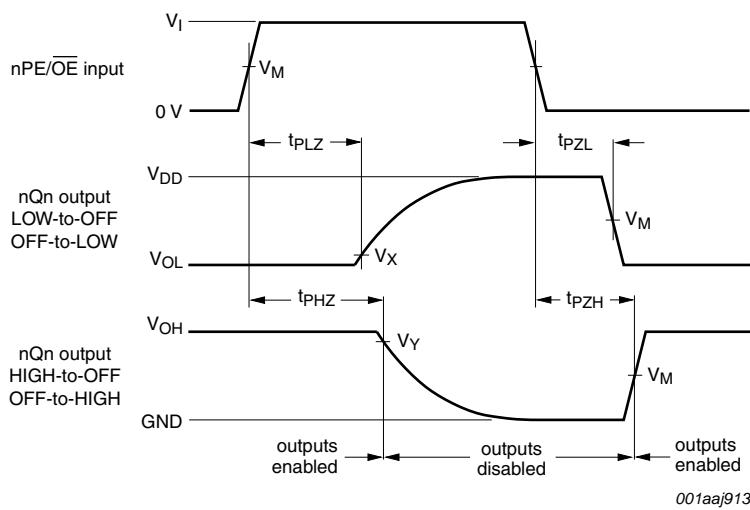


Fig 5. Enable and disable times and 3-state propagation delays

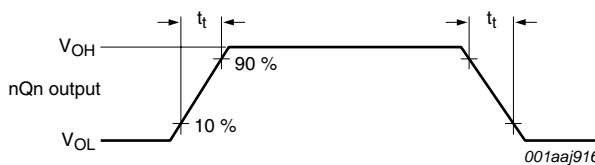


Fig 6. Transition times for nQn

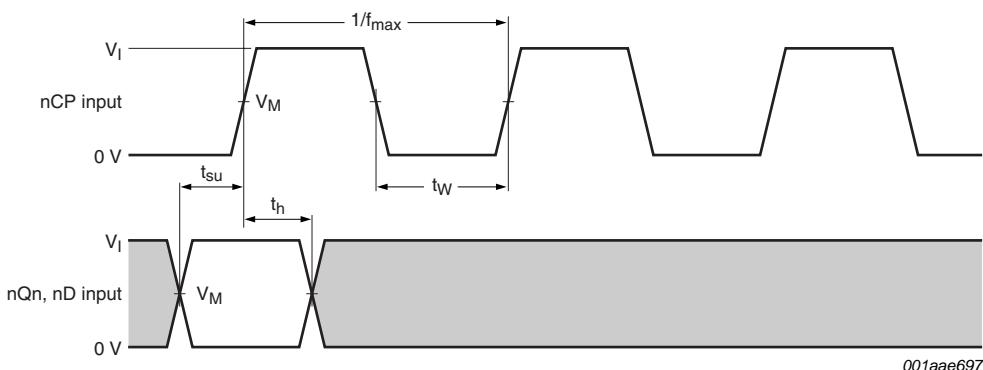
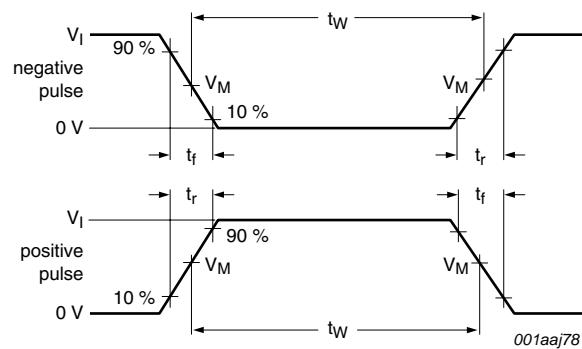
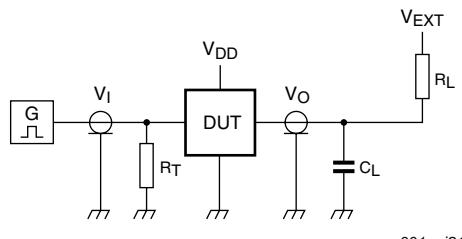


Fig 7. Waveforms showing minimum clock pulse width and maximum frequency and set-up and hold times for nQn (as data input) or nD to nCP



a. Input waveforms



b. Test circuit

Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

Fig 8. Test circuit for switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}		
	V_I	t_r, t_f	C_L	R_L		t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}
5 V to 15 V	V_{DD}	$\leq 20 \text{ ns}$	50 pF	1 k Ω	open	$2V_{DD}$	GND

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

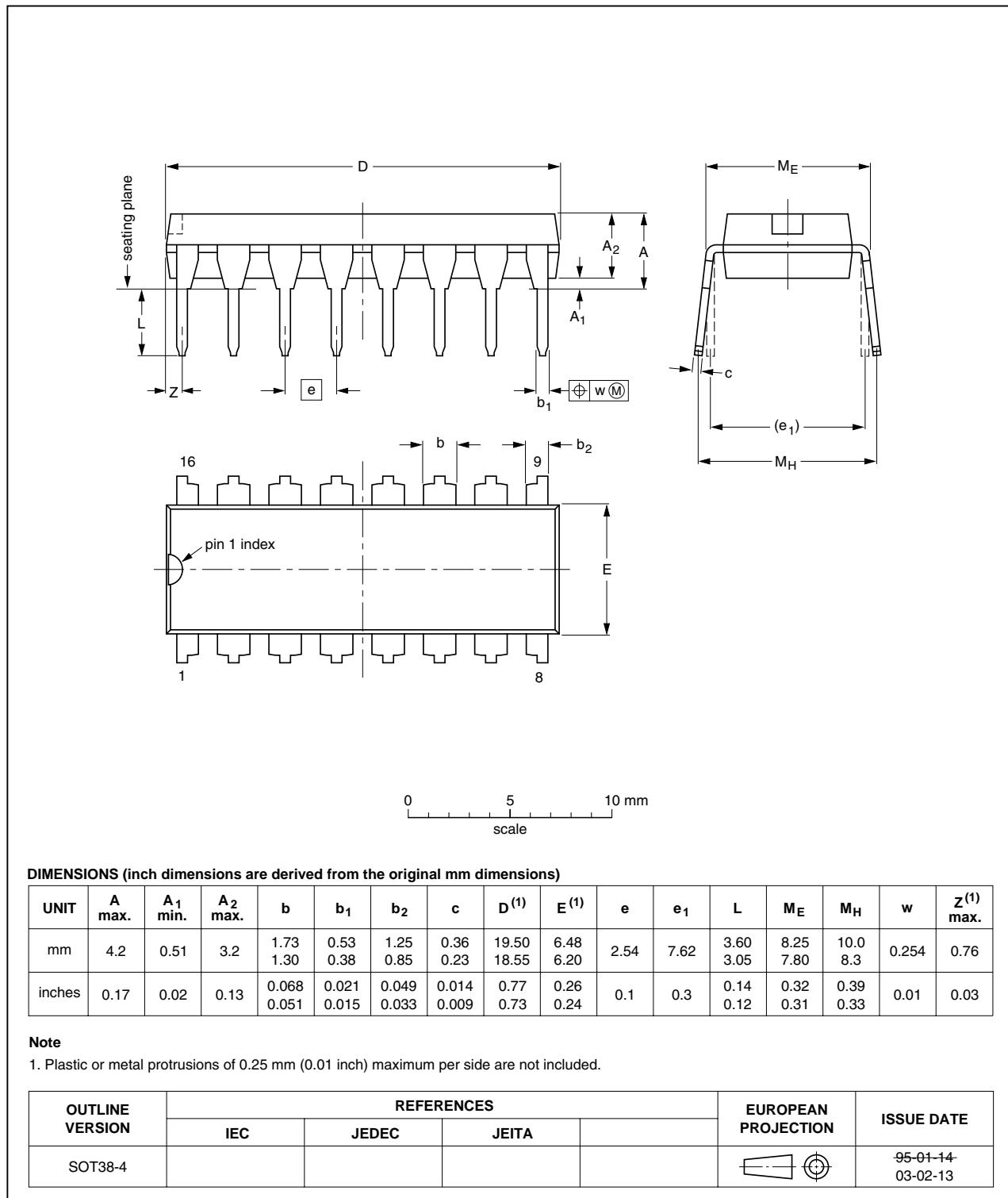


Fig 9. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 7.5 mm

SOT162-1

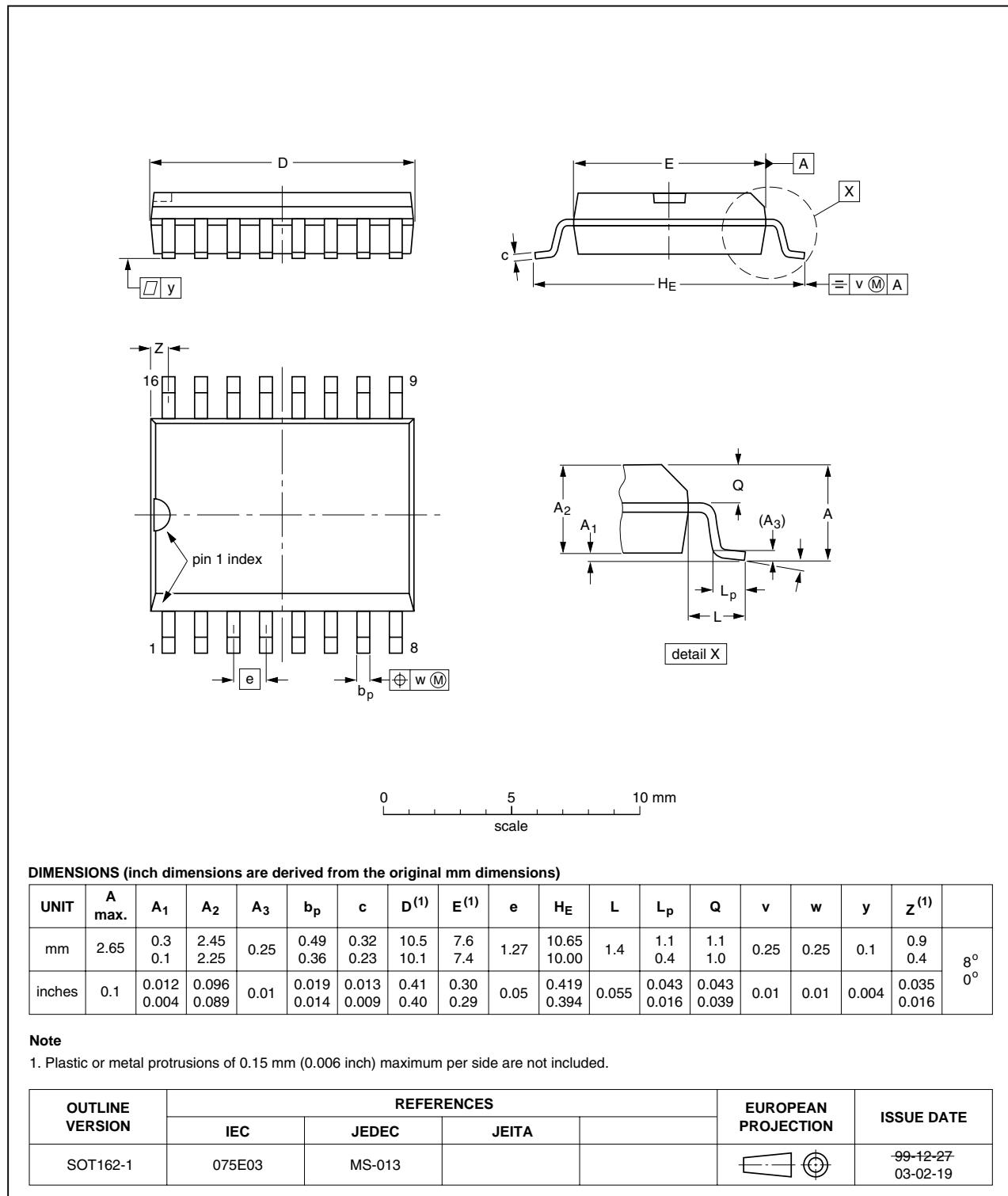


Fig 10. Package outline SOT162-1 (SO16)

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4517B_6	20091210	Product data sheet	-	HEF4517B_5
Modifications:	• Section 9 "Recommended operating conditions" Δt/ΔV values updated.			
HEF4517B_5	20090728	Product data sheet	-	HEF4517B_4
HEF4517B_4	20090406	Product data sheet	-	HEF4517B_CNV_3
HEF4517B_CNV_3	19950101	Product specification	-	HEF4517B_CNV_2
HEF4517B_CNV_2	19950101	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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